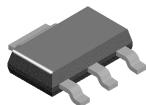
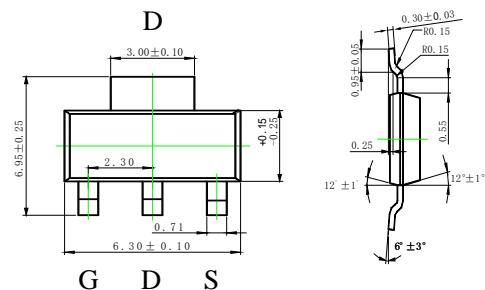


RoHS Compliant Product


**SOT-223**


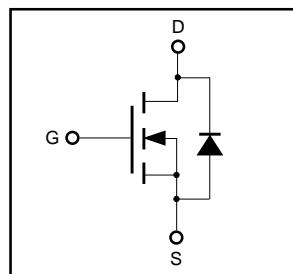
## Description

The SSM3055 Provide the designer with the best Combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SOT-223 Package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage application such as DC/DC conerters.

## Features

- \* Dynamic dv/dt Rating
- \* Simple Drive Requirement
- \* Repetitive Avalanche Rated
- \* Fast Switching



## Absolute Maximum Ratings

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> @10V	I <sub>D</sub> @T <sub>A</sub> =25°C	4	A
Continuous Drain Current, V <sub>GS</sub> @10V	I <sub>D</sub> @T <sub>A</sub> =75°C	3.2	A
Pulsed Drain Current <sup>1</sup>	I <sub>DM</sub>	20	A
Total Power Dissipation	P <sub>D</sub> @T <sub>A</sub> =25°C	2.7	W
Linear Derating Factor		0.02	W/°C
Operating Junction and Storage Temperature Range	T <sub>j</sub> , T <sub>stg</sub>	-55~+150	°C

## Thermal Data

Parameter	Symbol	Ratings	Unit
Thermal Resistance Junction-ambient	R <sub>thj-a</sub>	45	°C/W



**Elektronische Bauelemente**

**SSM3055**

**4A, 30V, RDS(ON) 80mΩ**

**N-Channel Enhancement Mode Power Mos.FET**

**Electrical Characteristics( Tj=25°C Unless otherwise specified)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	–	–	V	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA
Breakdown Voltage Temp. Coefficient	△BV <sub>Ds</sub> /△T <sub>j</sub>	–	0.037	–	V/°C	Reference to 25°C, I <sub>D</sub> =1mA
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	–	3.0	V	V <sub>Ds</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA
Gate-Source Leakage Current	I <sub>GSS</sub>	–	–	±100	nA	V <sub>GS</sub> =±20V
Drain-Source Leakage Current (Tj=25°C)	I <sub>DSS</sub>	–	–	25	uA	V <sub>DS</sub> =30V, V <sub>GS</sub> =0
Drain-Source Leakage Current (Tj=70°C)		–	–	250	uA	V <sub>DS</sub> =24V, V <sub>GS</sub> =0
Static Drain-Source On-Resistance	R <sub>Ds(ON)</sub>	–	–	80	mΩ	V <sub>GS</sub> =10V, I <sub>D</sub> =4A
		–	–	100		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A
Total Gate Charge <sup>2</sup>	Q <sub>g</sub>	–	5.4	–	nC	I <sub>D</sub> =4A V <sub>DS</sub> =24V V <sub>GS</sub> =5V
Gate-Source Charge	Q <sub>gs</sub>	–	1.3	–		
Gate-Drain ("Miller") Charge	Q <sub>gd</sub>	–	3.6	–		
Turn-on Delay Time <sup>2</sup>	T <sub>d(ON)</sub>	–	3.6	–	nS	V <sub>DD</sub> =15V I <sub>D</sub> =1A V <sub>GS</sub> =10V R <sub>G</sub> =3.3Ω R <sub>D</sub> =1.9Ω
Rise Time	T <sub>r</sub>	–	19.8	–		
Turn-off Delay Time	T <sub>d(OFF)</sub>	–	13	–		
Fall Time	T <sub>f</sub>	–	3.2	–		
Input Capacitance	C <sub>iss</sub>	–	260	–	pF	V <sub>GS</sub> =0V V <sub>DS</sub> =25V f=1.0MHz
Output Capacitance	C <sub>oss</sub>	–	144	–		
Reverse Transfer Capacitance	C <sub>rss</sub>	–	13	–		

**Source-Drain Diode**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Condition
Forward On Voltage <sup>2</sup>	V <sub>Ds</sub>	–	–	1.3	V	V <sub>s</sub> =2A, V <sub>GS</sub> =0V, T <sub>j</sub> =25
Continuous Source Current(Body Diode)	I <sub>s</sub>	–	–	4	A	V <sub>D</sub> =V <sub>G</sub> =0V, V <sub>s</sub> =1.3V
Pulsed Source Current (Body Diode) <sup>1</sup>	I <sub>SM</sub>	–	–	20	A	

Notes: 1.Pulse width Limited by safe operating area.

2.Pulse width ≤300us, dutycycle≤2%.

# SECOOS

Elektronische Bauelemente

# SSM3055

4A, 30V, RDS(ON) 80mΩ

N-Channel Enhancement Mode Power Mos.FET

## Characteristics Curve

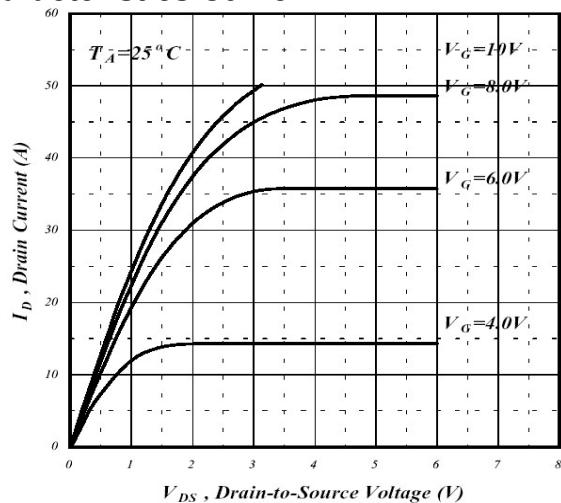


Fig 1. Typical Output Characteristics

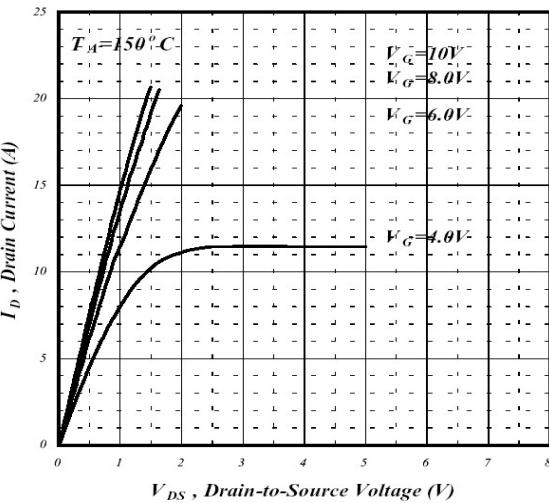


Fig 2. Typical Output Characteristics

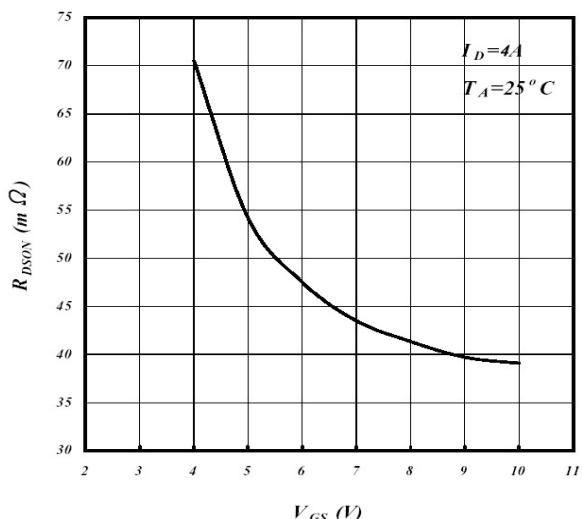


Fig 3. On-Resistance v.s. Gate Voltage

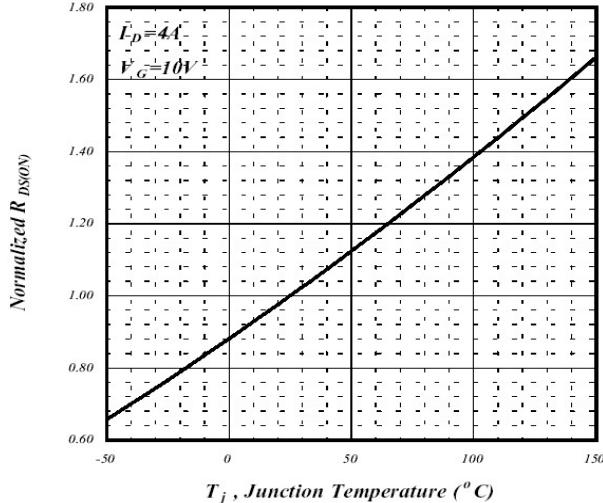


Fig 4. Normalized On-Resistance v.s. Junction Temperature

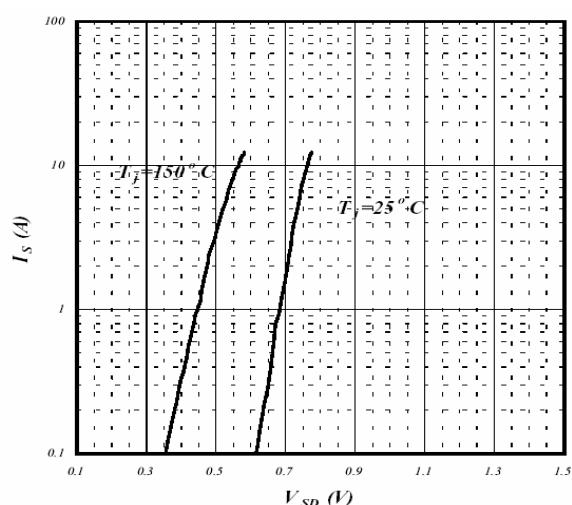


Fig 5. Forward Characteristics of Reverse Diode

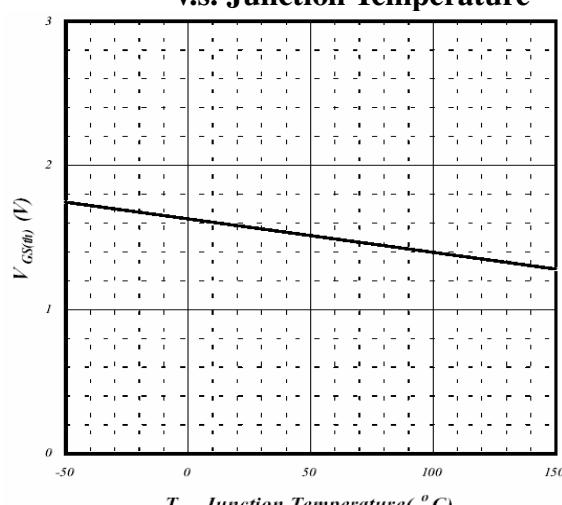


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

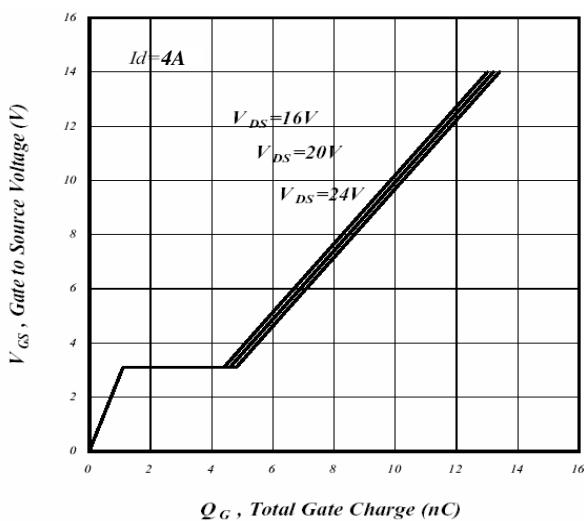
# SECOOS

Elektronische Bauelemente

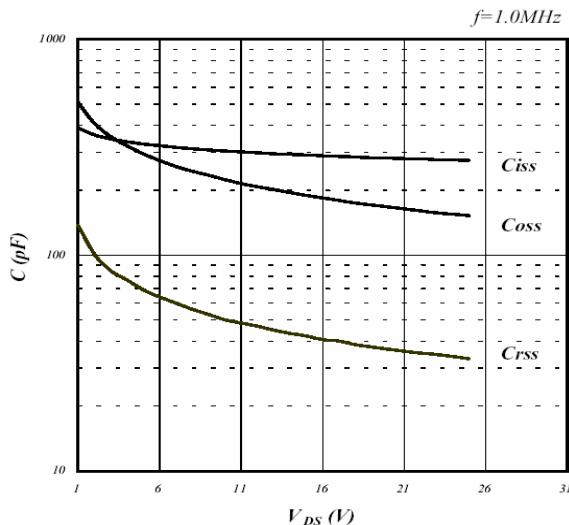
# SSM3055

4A, 30V,RDS(ON) 80mΩ

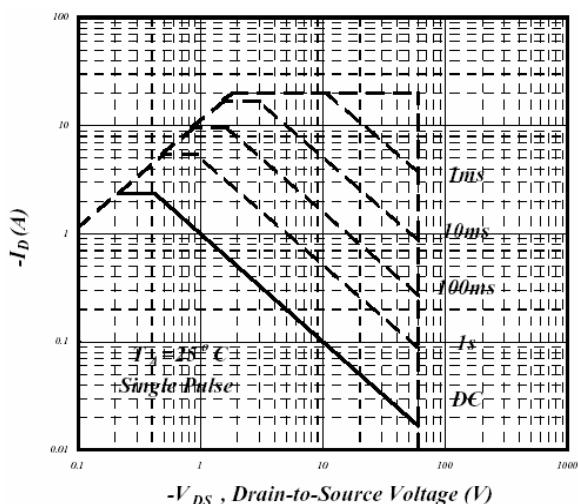
N-Channel Enhancement Mode Power Mos.FET



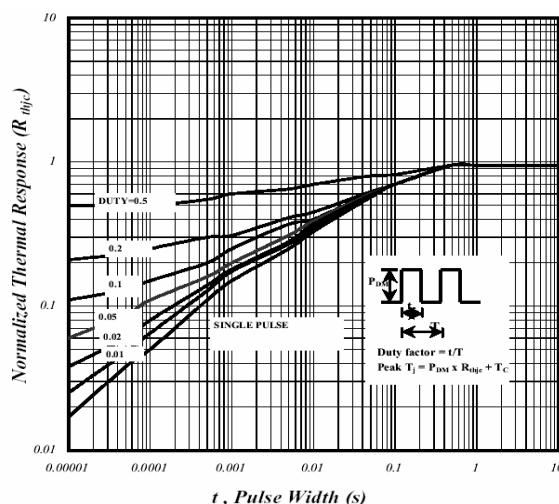
**Fig 7. Gate Charge Characteristics**



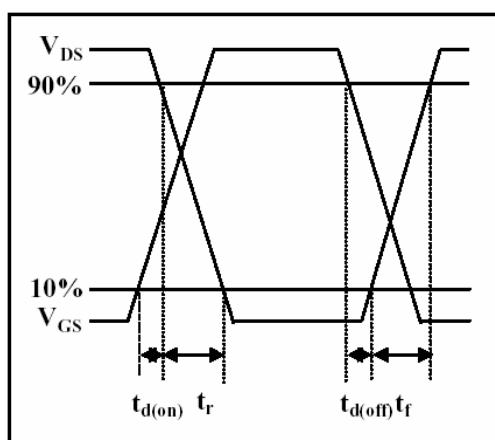
**Fig 8. Typical Capacitance Characteristics**



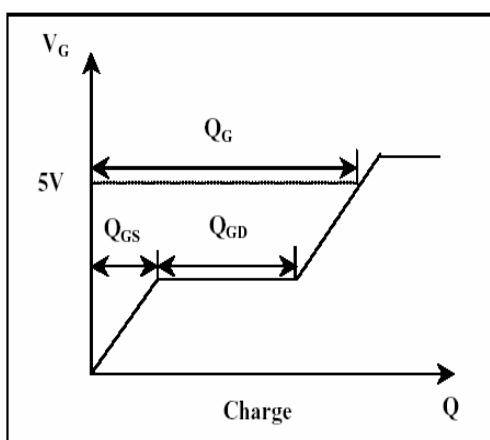
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



**Fig 11. Switching Time Circuit**



**Fig 12. Gate Charge Waveform**